Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Low threshold voltage
- Extended temperature range T_i = 175 °C
- Trench MOSFET technology
- Very fast switching
- AEC-Q101 qualified

3. Applications

- Relay driver
- · High-speed line driver
- · High-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-------------------|----------------------------------|--|-----|-----|-----|------|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | - | -20 | V |
| V _{GS} | gate-source voltage | | | -12 | - | 12 | V |
| I _D | drain current | V _{GS} = -4.5 V; T _{amb} = 25 °C | [1] | - | - | -4.9 | Α |
| Static characte | Static characteristics | | | | | | |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = -4.5 \text{ V}; I_D = -4.9 \text{ A}; T_j = 25 \text{ °C}$ | | - | 30 | 38 | mΩ |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--------------------|-----------------|
| 1 | G | gate | 3 | D - |
| 2 | S | source | | |
| 3 | D | drain | | G P |
| | | | 1 2 | \$ 017aaa257 |
| | | | SOT23 | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | | |
|-------------|---------|--|---------|--|--|--|
| | Name | Description | Version | | | |
| PMV30XPA | SOT23 | plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body | SOT23 | | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code[1] |
|-------------|-----------------|
| PMV30XPA | %НН |

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|----------------------|--|---|-----|-----|------|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | -20 | V |
| V_{GS} | gate-source voltage | | | -12 | 12 | V |
| I _D | drain current | V _{GS} = -4.5 V; T _{amb} = 25 °C | [1] | - | -4.9 | А |
| | | V _{GS} = -4.5 V; T _{amb} = 100 °C | [1] | - | -3.1 | А |
| I _{DM} | peak drain current | T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$ | | - | -20 | А |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [2] | - | 610 | mW |
| | | | [1] | - | 1.4 | W |
| | | T _{sp} = 25 °C | | - | 8.3 | W |
| Tj | junction temperature | | | -55 | 175 | °C |
| T _{amb} | ambient temperature | | | -55 | 175 | °C |
| T _{stg} | storage temperature | | | -65 | 175 | °C |
| Source-drain | n diode | | | | | |
| Is | source current | T _{amb} = 25 °C | [1] | - | -1.5 | Α |
| ESD maximu | ım rating | | | | | |
| V _{ESD} | electrostatic discharge voltage | НВМ | [3] | - | 500 | V |
| Avalanche ru | ıggedness | | | ' | | ' |
| E _{DS(AL)S} | non-repetitive drain- source avalanche energy | $T_{j(init)}$ = 25 °C; I_D = -1.5 A; DUT in avalanche (unclamped) | | - | 15.5 | mJ |

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

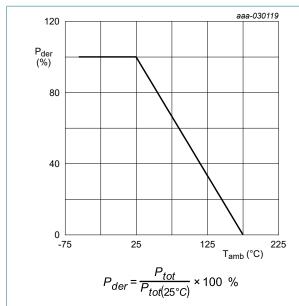


Fig. 1. Normalized total power dissipation as a function of ambient temperature

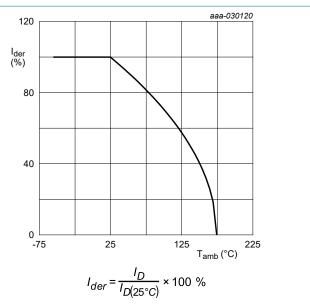


Fig. 2. Normalized continuous drain current as a function of ambient temperature

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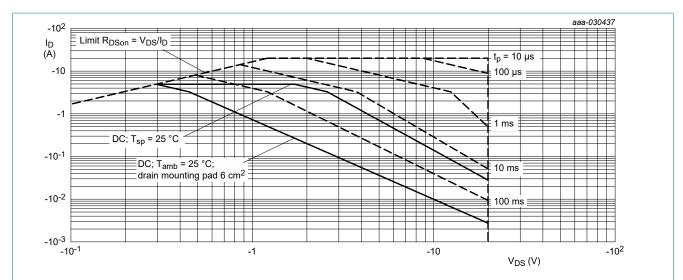


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

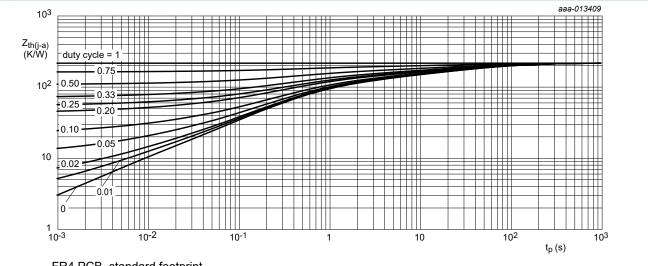
20 V, P-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

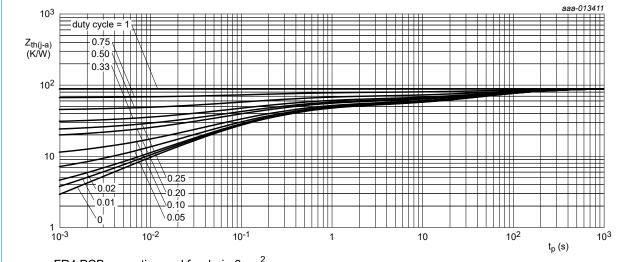
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|--|-------------|-----|-----|-----|-----|------|
| R _{th(j-a)} | thermal resistance from | in free air | [1] | - | 208 | 245 | K/W |
| junction to ambient | junction to ambient | | [2] | - | 88 | 104 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | 13 | 18 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm²

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|-----------------------------------|---|------|-------|------|------|
| Static chara | acteristics | | | | | |
| V _{(BR)DSS} | drain-source breakdown voltage | I_D = -250 μ A; V_{GS} = 0 V; T_j = 25 °C | -20 | - | - | V |
| V_{GSth} | gate-source threshold voltage | I_D = -250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C | -0.6 | -0.95 | -1.3 | V |
| I _{DSS} | drain leakage current | V _{DS} = -20 V; V _{GS} = 0 V; T _j = 25 °C | - | - | -1 | μΑ |
| I _{GSS} | gate leakage current | V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C | - | - | -100 | nA |
| | | V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 100 | nA |
| R _{DSon} | drain-source on-state | $V_{GS} = -8 \text{ V}; I_D = -4.9 \text{ A}; T_j = 25 ^{\circ}\text{C}$ | - | 25 | 33 | mΩ |
| | resistance | V _{GS} = -8 V; I _D = -4.9 A; T _j = 175 °C | - | 40 | 53 | mΩ |
| | | V_{GS} = -4.5 V; I_D = -4.9 A; T_j = 25 °C | - | 30 | 38 | mΩ |
| | | $V_{GS} = -2.5 \text{ V}; I_D = -3 \text{ A}; T_j = 25 ^{\circ}\text{C}$ | - | 45 | 62 | mΩ |
| 9 _{fs} | forward transconductance | V_{DS} = -10 V; I_{D} = -4.9 A; T_{j} = 25 °C | - | 18 | - | S |
| R_{G} | gate resistance | f = 1 MHz | - | 6 | - | Ω |
| Dynamic ch | aracteristics | | | | | |
| Q _{G(tot)} | total gate charge | $V_{DS} = -10 \text{ V}; I_D = -5 \text{ A}; V_{GS} = -4.5 \text{ V};$ | - | 11 | 16 | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C | - | 1.9 | - | nC |
| Q_{GD} | gate-drain charge | | - | 3.4 | - | nC |
| C _{iss} | input capacitance | V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V; | - | 1039 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 124 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 110 | - | pF |
| t _{d(on)} | turn-on delay time | V _{DS} = -10 V; I _D = -5 A; V _{GS} = -4.5 V; | - | 8 | - | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$ | - | 30 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 40 | - | ns |
| t _f | fall time | | - | 23 | - | ns |
| Source-drai | in diode | | ' | | | |
| V_{SD} | source-drain voltage | $I_S = -1.5 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | -0.8 | -1.2 | V |
| t _{rr} | reverse recovery time | I _S = -1.5 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V; V _{DS} = -10 V; T _j = 25 °C | - | 13 | - | ns |
| Q _r | recovered charge | dI _S /dt = -100 A/μs; V _{GS} = 0 V; V _{DS} = -10 V; T _i = 25 °C | - | 3 | - | nC |

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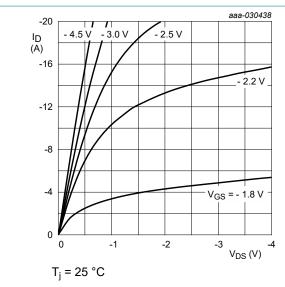


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

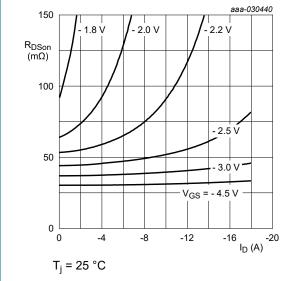


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

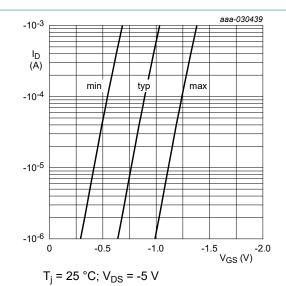


Fig. 7. Subthreshold drain current as a function of gate-source voltage

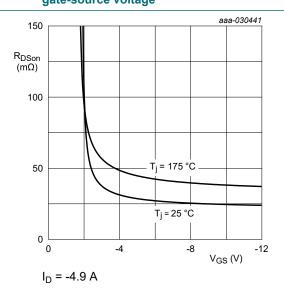


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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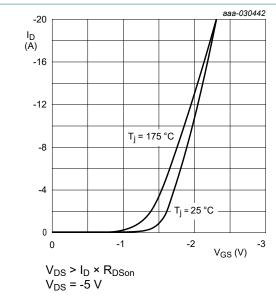


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

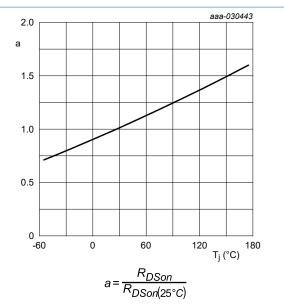


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

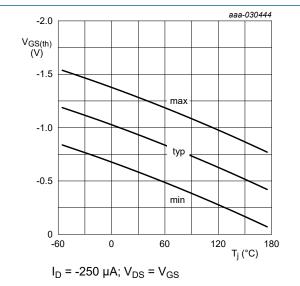


Fig. 12. Gate-source threshold voltage as a function of junction temperature

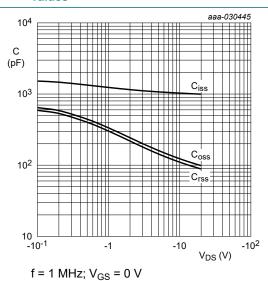


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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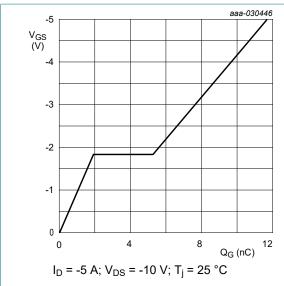


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$

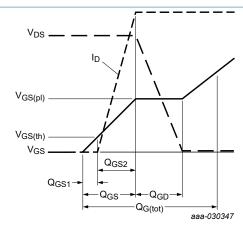


Fig. 15. Gate charge waveform definitions

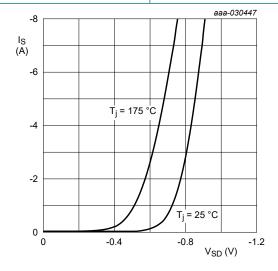
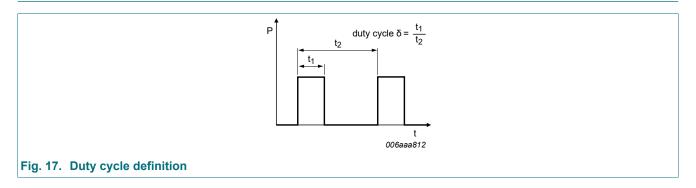


Fig. 16. Source current as a function of source-drain voltage; typical values

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11. Test information



Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

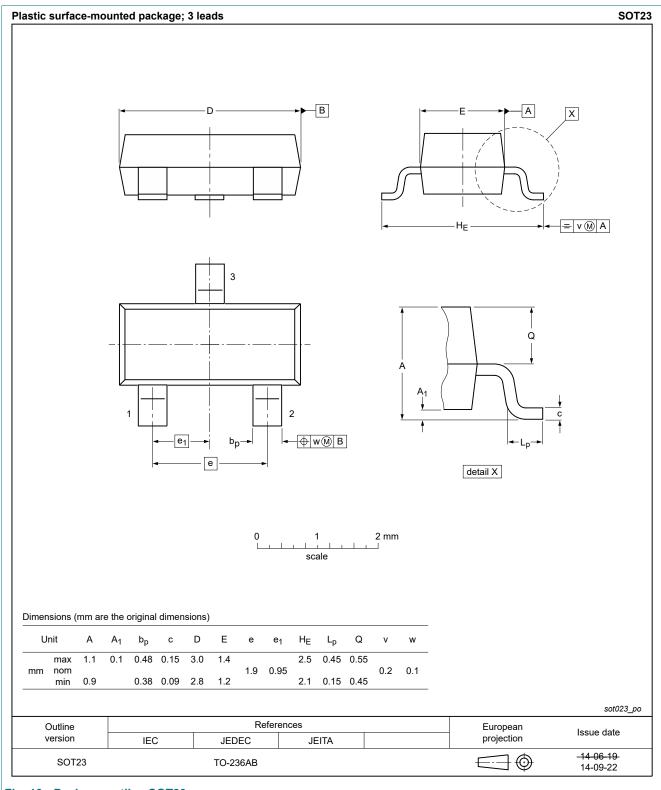
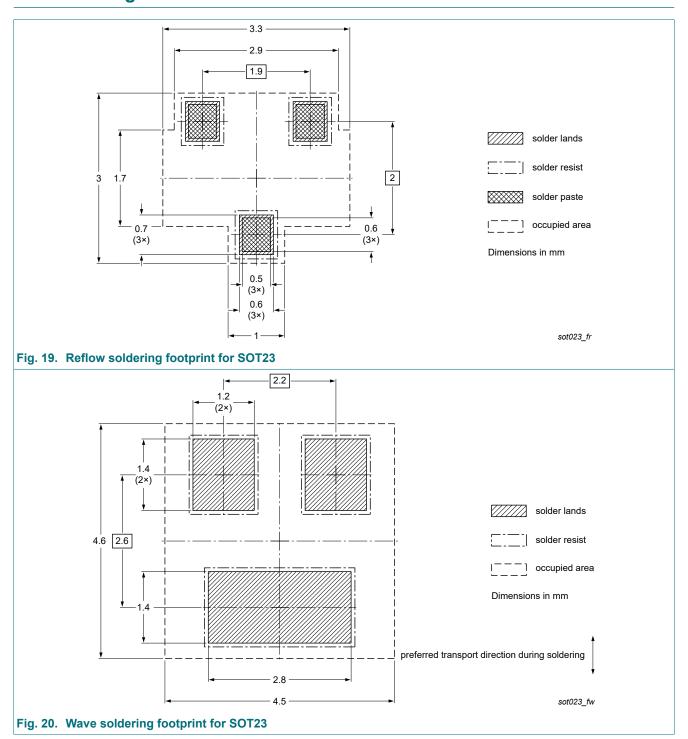


Fig. 18. Package outline SOT23

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13. Soldering



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14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes | | | |
|----------------|----------------|--|---------------|--------------|--|--|--|
| PMV30XPA v.2 | 20200320 | Product data sheet | - | PMV30XPA v.1 | | | |
| Modifications: | Characteristic | Characteristics: "Gate resistance" corrected | | | | | |
| PMV30XPA v.1 | 20200107 | Product data sheet | - | - | | | |

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15. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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